Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("5670297").PN.	USPAT	OR	OFF	2005/12/08 20:42
S1	7	("2150017").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 12:46
S2	0	("jp2150017"):PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 12:46
S3	0	("jp2150017").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 12:46
S4	0	("jp2150017").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 12:47
S5	13	(("5413958") or ("5529630") or ("5595923") or ("5767930") or ("5854494") or ("5966594") or ("5854096") or ("5712191") or ("5731613") or ("5937282") or ("5959313") or ("6051453") or ("6071764")).PN.	USPAT	OR	OFF	2005/01/07 12:59
S6	18396	((438/128) or (438/149) or (438/151) or (438/154) or (438/164) or (438/174) or (438/180) or (438/181) or (438/194) or (438/197) or (438/199) or (438/275) or (438/229) or (438/275) or (438/287) or (438/289) or (438/289) or (438/290) or (438/291) or (438/299) or (438/301) or (438/311) or (438/364) or (438/378) or (438/378) or (438/479) or (438/491) or (438/491) or (438/514) or (438/517) or (438/778) or (438/791) or (438/795)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/10 18:20

S7	4706	S6 and (p adj type same ((ion near2 implant\$5) or implant\$5 or dop\$3)) same ((semiconductor or silicon or polysilicon or polycrystalline or (single near2 crystal\$4) or (mono near2 crystal\$4)) same(region\$1 or layer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 18:21
S8	364	S7 and (active near2 matrix)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 18:21
S9	61	S8 and ((lcd or (liquid adj crystal adj display)) and (image near2 sensor) and (electro adj optical adj device))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 18:22
S10	3	("4727044"   "5147826"   "5313076").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/07 13:42
S11	301	S8 not S9 .	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/07 13:42
S12	4261	((conductive near (layer\$1 or film\$1)) or contact\$1 or electrod\$2) same (("Ti" or titanium) and ("Al" or aluminum)) same (interlayer\$1 or passivat\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 14:22
S13	1132	S12 and (active near matrix)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 14:24
S14	93	S13 and (image near sensor) and (electro adj optical) and ("LCD" or liquid adj crystal adj device\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 17:29
S15	93	S13 and ((image near sensor) and (electro adj optical) and ("LCD" or liquid adj crystal adj device\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 14:26

S16	0	S14 not S13	US-PGPUB; USPAT;	OR	ON	2005/01/31 14:32
			USOCR; EPO; JPO; DERWENT; IBM_TDB			
S17	1039	S13 not S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 14:33
S18	1039	S17 and (active near matrix)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 14:34
S19	2	("6081308"   "6380007").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/31 14:57
S20	437	(image near sensor) and (electro adj optical) and ("LCD" or liquid adj crystal adj device\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:49
S21	248	S20 and (active adj matrix)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 17:38
S22	248	S21 not "Semiconductor Energy Laboratory Co., LTD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 17:38
S23	O	"Semiconductor Energy Laboratory Co., Ltd" not S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/31 17:38

S24	19677	((438/128) or (438/149) or	US-PGPUB;	OR	OFF	2005/07/10 18:20
		(438/151) or (438/154) or (438/164) or (438/174) or (438/180) or (438/181) or (438/194) or (438/197) or (438/199) or (438/275) or (438/276) or (438/278) or (438/287) or (438/289) or (438/290) or (438/291) or (438/299) or (438/301) or (438/311) or (438/364) or (438/378) or (438/378) or (438/378) or (438/378) or (438/378) or (438/378) or (438/517) or (438/778) or (438/791) or (438/795)).CCLS.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			
S25	5110	S24 and (p adj type same ((ion near2 implant\$5) or implant\$5 or dop\$3)) same ((semiconductor or silicon or polysilicon or polycrystalline or (single near2 crystal\$4) or (mono near2 crystal\$4)) same(region\$1 or layer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 18:21
S26	420	S25 and (active near2 matrix)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 18:21
S27	71	S26 and ((lcd or (liquid adj crystal adj display)) and (image near2 sensor) and (electro adj optical adj device))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 18:22
S28	13	(("5413958") or ("5529630") or ("5595923") or ("5767930") or ("5854494") or ("5966594") or ("5854096") or ("5712191") or ("5731613") or ("5937282") or ("5959313") or ("6051453") or ("6071764")).PN.	USPAT	OR	OFF	2005/07/10 18:23

		<u> </u>	1	I	Γ	T
S29	20964	((438/142) or (438/149) or (438/151) or (438/154) or (438/164) or (438/197) or (438/199) or (438/309) or (438/301) or (438/514) or (438/517) or (438/532) or (438/585) or (438/586) or (438/587) or (438/597) or (438/618) or (438/637) or (438/652) or (438/685) or (438/688) or (438/758) or (438/758) or (438/758) or (438/758) or (438/758) or (438/758).	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 13:38
S30	482	S29 and (((active adj matrix) or "LCD" or (liquid adj crystal)) same (interlayer\$1 or passivat\$3 or (multi adj (layer\$1 or interlayer\$1))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:55
S31	52	S30 and ((("Ti" or titanium) or ("Al" or aluminum)) near5 (interlayer\$1 or passivat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:34
S32	482	S29 and (((active adj matrix) or "LCD" or (liquid adj crystal)) same (interlayer\$1 or passivat\$3 or (multi adj (layer\$1 or interlayer\$1)) or ((("SiN" or (silicon adj nitride)) or ("SiO" or (silicon adj oxide))) near5 interlayer\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:47
S33	52	S32 and ((("Ti" or titanium) or ("Al" or aluminum)) near5 (interlayer\$1 or passivat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:48
<b>534</b>	9282	(((active adj matrix) or "LCD" or (liquid adj crystal)) same (interlayer\$1 or passivat\$3 or (multi adj (layer\$1 or interlayer\$1)) or ((("SiN" or (silicon adj nitride)) or ("SiO" or (silicon adj oxide))) near5 interlayer\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:47
S35	557	S34 and ((("Ti" or titanium) or ("Al" or aluminum)) near5 (interlayer\$1 or passivat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:56

S36	505	S35 not S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:48
S37	17	S36 and (image near sensor) and (electro adj optical)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:49
S38	37	S29 and (((active adj matrix) or "LCD" or (liquid adj crystal)) same ((first adj interlayer) and (second adj interlayer)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:57
S39	4	S38 and ((("Ti" or titanium) or ("Al" or aluminum)) near5 (interlayer\$1 or passivat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 17:57
S40	352	(((active adj matrix) or "LCD" or (liquid adj crystal)) same ((first adj interlayer) and (second adj interlayer)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 18:00
S41	52	S40 and ((("Ti" or titanium) or ("Al" or aluminum)) near5 (interlayer\$1 or passivat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 18:00
S42	2380	(((active adj matrix) or "LCD" or (liquid adj crystal)) and ((first adj interlayer) and (second adj interlayer)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 18:00
S43	218	S42 and ((("Ti" or titanium) or ("Al" or aluminum)) near5 (interlayer\$1 or passivat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 18:01

S44 <sub>.</sub>	166	S43 not S41	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 18:39
S45	2	(("6596572") or ("5767529")).PN.	USPAT	OR	OFF	2005/12/03 13:41
S46	13	("5413958"   "5529630"   "5595923"   "5712191"   "5731613"   "5767930"   "5854096"   "5854494"   "5937282"   "5959313"   "5966594"   "6051453"   "6071764").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/03 13:42
S47	4	("5767529").URPN.	USPAT	OR	OFF	2005/12/03 13:43
S48	192	(cmos near5 (active adj matrix))	USPAT	OR	OFF	2005/12/05 13:32
S49	31	(cmos near5 (active adj matrix adj circuit))	USPAT	OR	OFF	2005/12/05 13:38
S50	20964	((438/142) or (438/149) or (438/151) or (438/154) or (438/164) or (438/197) or (438/199) or (438/299) or (438/301) or (438/308) or (438/479) or (438/514) or (438/517) or (438/532) or (438/585) or (438/586) or (438/587) or (438/587) or (438/637) or (438/638) or (438/658) or (438/658) or (438/658) or (438/758) or (438/761) or (438/778)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/06 12:56
S51	56	S50 and (((p adj type) or boron) near5 ((active adj matrix adj circuit) or pixel\$1 or (pixel adj electrode\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 13:44
S52	480	(438/761).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/06 13:06
S53	1291	(438/151).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/06 13:18

S54	715	(438/597).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/06 13:29
S55	2262	(438/586).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/06 13:49
S56	2461	(438/637).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/06 13:49